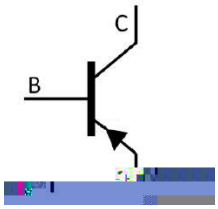
WR0<50P ṂṂ Ł SQS ÆṀ ɥ s ǁ ˥ Silicon PNP transistor in a TO-92LM Plastic Package.

ت ᵊ я ᴗ Ӈ/Ȁ ҩ`Н ҫ˜ /ѣ NWF653< Ӥ ´
Low collector saturation, high speed switching time, complementary to KTC3209.

ҭ̂ ̂ ̂ ı ' ѿ ᵊ/ɔ ◊ Ȁ ҩ
Power amplifier and switching applications.



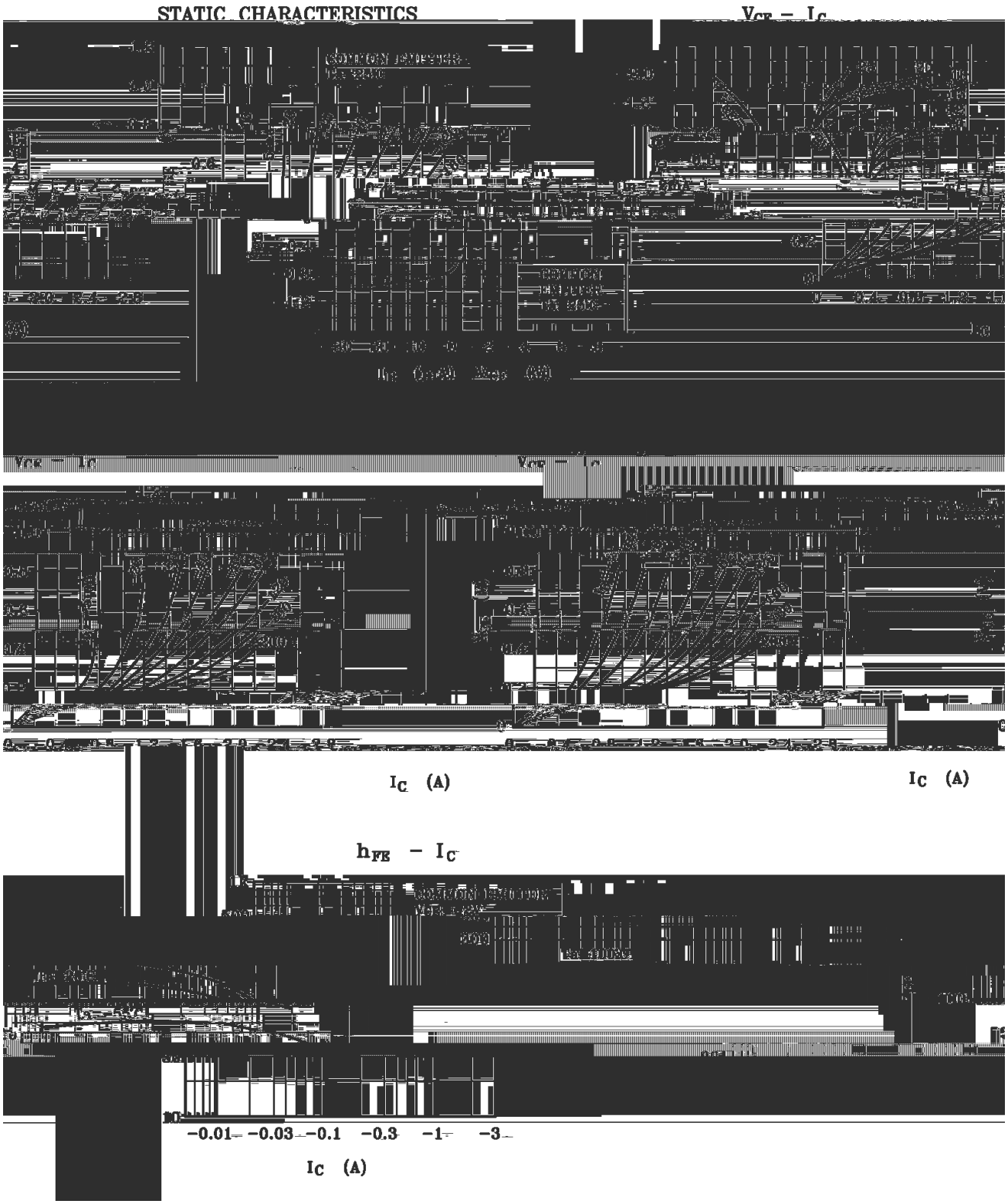


PIN1 χ Base PIN 2 χ Collector -1382alec4lec040607e71 Tf2.2229 0 TD0 Tf1 Tf2.2229 0 T4MarE73

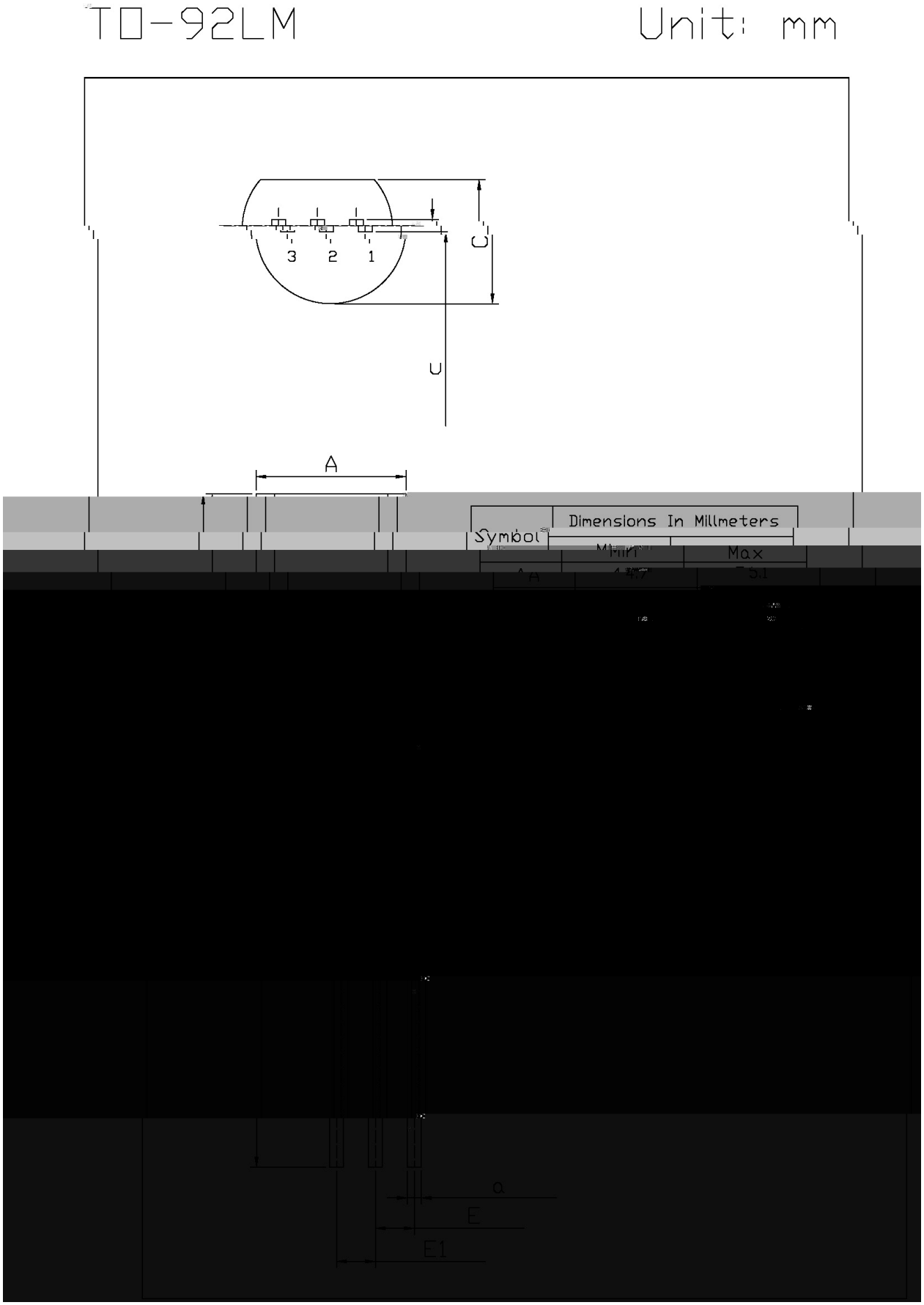
v ̈Ω̣ Parameter	⊣ N Symbol	̈Ω̣Ö Rating	D Ĥ Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̈Ω̣	⊣ N	⊥ ⁝ ̌ Ţ	ω ṇ Ö Ɛ ʒ Ö
Parameter	Symbol	Test Conditions	Min

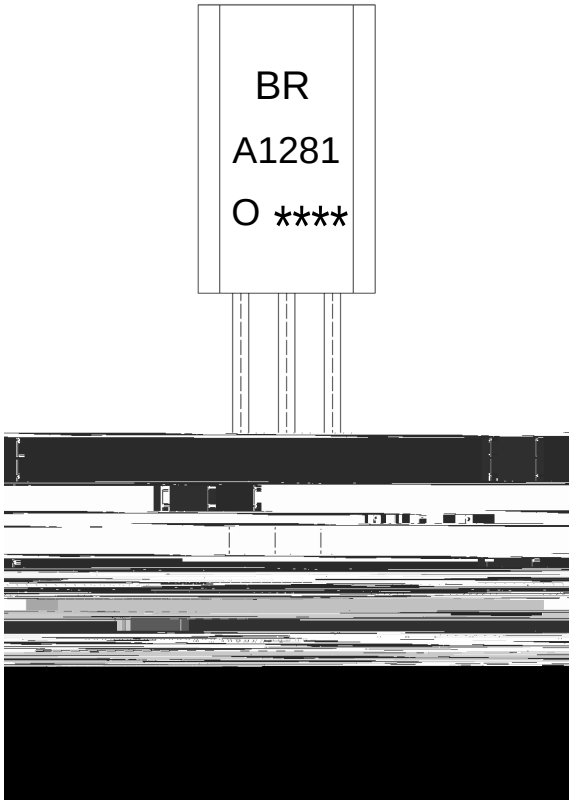
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



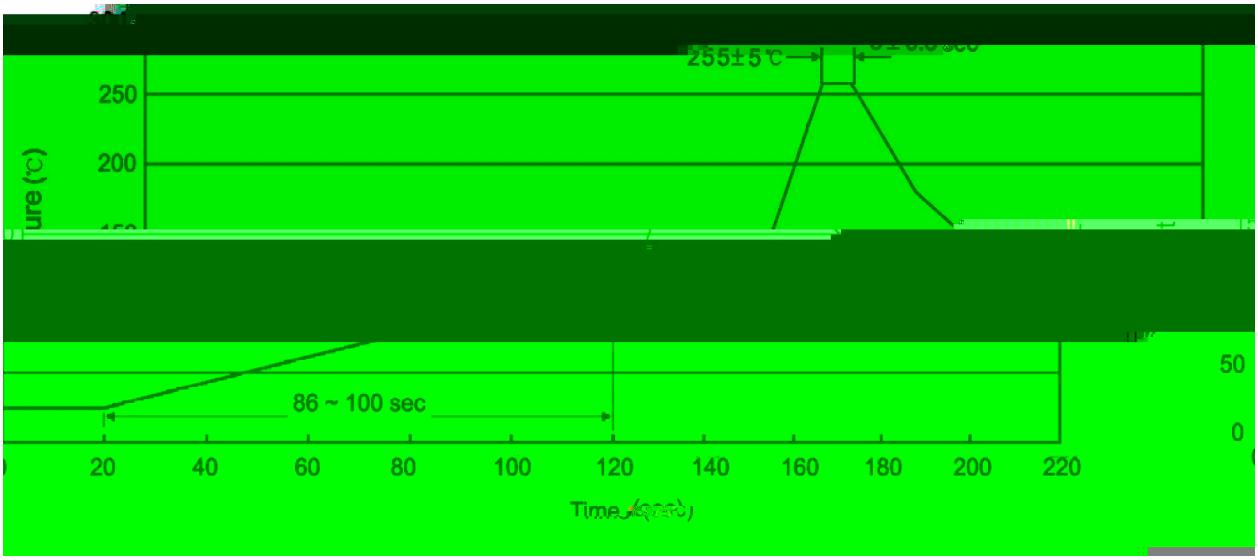
ب ˝ χ

EU=	ѭ ʒ ᴵ Ɱ
D45 ; 4 χ	ѭ ʒ ᴺ Ɱ
R=	ѭ k_{IH} ʿ ᶠ Ɱ
---- χ	ѭ ɨ ɾ ŋ̈ ᴺ Ɱ ɪ ɞ ɨ ɾ ŋ̈ ᴺ ψ ק

Note:

BR:	Company Code.
A1281:	Product Type.
O:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 ǂ ♬ □ ỷ 25 Ḱ 150 ɬ ı `H ڑ 60 Ḱ 90sec;

2 Š Ö □ ỷ 255 ° 5 ɬ ı `H ڑ ˋY ⺈ ⺮ 5 ° 0.5sec;

3 ì ˙ ⺈ ˛ ɔ ھ ỷ ⺮ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ɬ `H ڑ χ 10 ° 1 sec. Temp.:270 ° 5 ɬ Time:10 ° 1 sec

/ Packaging SPEC.

ˋΩ ţ γ ŧ / BULK

Package Type	Units					Dimension (unit mm3)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92LM	1,000	8	8,000	5	40,000	135×190	237×172×102	560×245×195

⺈ Ṿ γ ŧ / AMMO

Package Type	Units					Dimension (unit mm3)	
	Units/tape /	Tape/Inner Box /	Rows/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Inner Box	Outer Box
TO-92LM	2,500	1	100	10	25,000	328×230×42	480×346×235 547×407×268

/ Notices